



ZTX694B

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$)

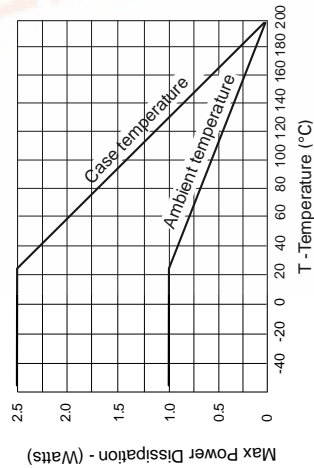
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	130			MHz	$I_C=50mA, V_{CE}=5V$ $f=50MHz$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5V, f=1MHz$
Output Capacitance	C_{obo}		9		pF	$V_{CB}=10V, f=1MHz$
Switching Times	t_{on}		80		ns	$I_C=100mA, I_B=10mA$ $I_{BZ}=10mA, V_{CE}=50V$
	t_{off}		2900		ns	

Measured under pulsed conditions. Pulse width=300us. Duty cycle $\leq 2\%$

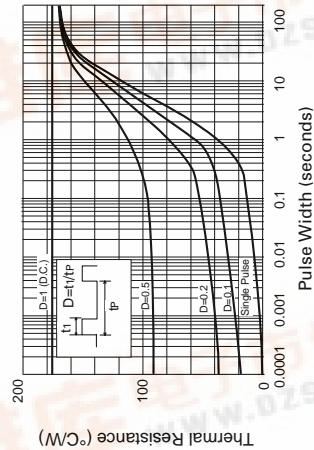
HERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)1}$	175	$^{\circ}C/W$
Junction to Ambient ₂	$R_{th(j-amb)2}$	116	$^{\circ}C/W$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}C/W$

Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



Derating curve



Maximum transient thermal impedance

NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ISSUE 1 - APRIL 94

FEATURES

- * 120 Volt V_{CEO}
- * Gain of 400 at $I_C=200mA$
- * Very low saturation voltage

APPLICATIONS

- * Darlington replacement
- * Relay / solenoid driver
- * Battery powered circuits
- * Motor drivers

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1	A
Continuous Collector Current	I_C	0.5	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

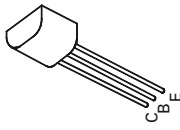
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	120			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=100V$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25		V	$I_C=100mA, I_B=0.5mA^*$
			0.5		V	$I_C=400mA, I_B=5mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=1A, I_B=10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=1A, V_{CE}=2V^*$
Static Forward Current Transfer Ratio	h_{FE}	500				$I_C=100mA, V_{CE}=2V^*$
		400				$I_C=200mA, V_{CE}=2V^*$
		150				$I_C=400mA, V_{CE}=2V^*$

查询ZTX694B供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

ZTX694B



E-Line
TO92 Compatible

ZTX694B

NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ZTX694B

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

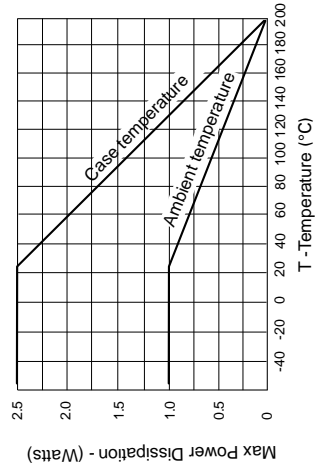
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	130			MHz	$I_C=50\text{mA}$, $V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5\text{V}$, $f=1\text{MHz}$
Output Capacitance	C_{obo}		9		pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$
Switching Times	t_{on}	80			ns	$I_C=100\text{mA}$, $I_B=10\text{mA}$
	t_{off}	2900			ns	$I_B=10\text{mA}$, $V_{CE}=50\text{V}$

Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$

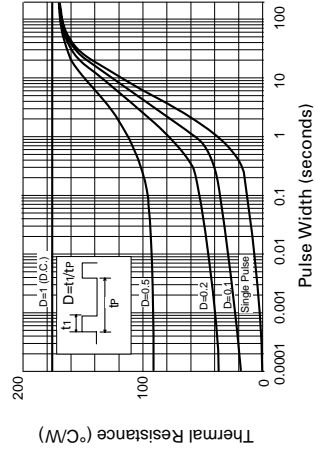
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)_1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient ₂	$R_{th(j-amb)_2}$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



Derating curve



Maximum transient thermal impedance

FEATURES

- * 120 Volt V_{CEO}
 - * Gain of 400 at $I_C=200\text{mA}$
 - * Very low saturation voltage
- ## APPLICATIONS
- * Darlington replacement
 - * Relay / solenoid driver
 - * Battery powered circuits
 - * Motor drivers

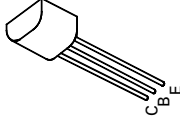
ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1	A
Continuous Collector Current	I_C	0.5	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation $T_{amb}=25^{\circ}\text{C}$ derate above 25°C	P_{tot}	1 5.7	W mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200	$^{\circ}\text{C}$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

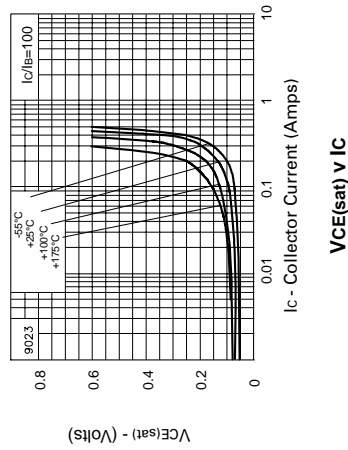
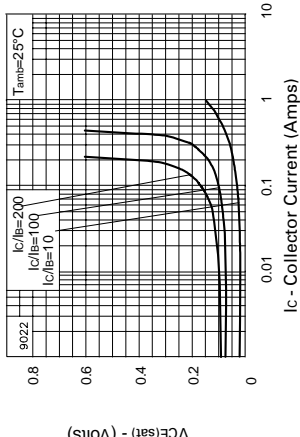
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	120			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=100\text{V}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25 0.5		V	$I_C=100\text{mA}$, $I_B=0.5\text{mA}^*$ $I_C=400\text{mA}$, $I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=1\text{A}$, $I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=1\text{A}$, $V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	500				$I_C=100\text{mA}$, $V_{CE}=2\text{V}^*$
		400				$I_C=200\text{mA}$, $V_{CE}=2\text{V}^*$
		150				$I_C=400\text{mA}$, $V_{CE}=2\text{V}^*$



E-Line
TO92 Compatible

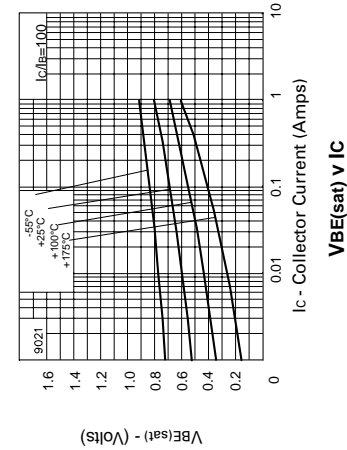
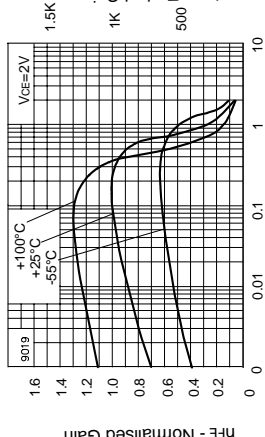
ZTX694B

TYPICAL CHARACTERISTICS



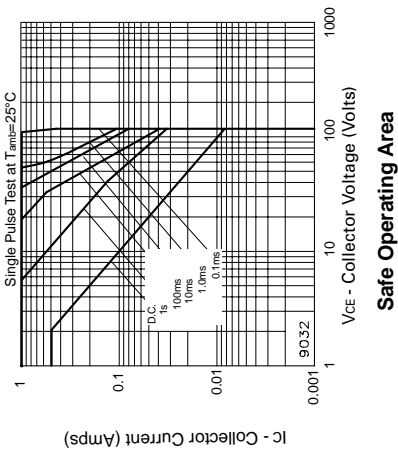
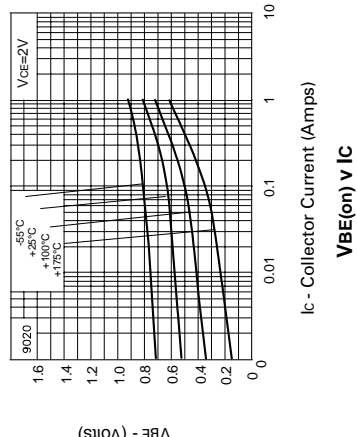
VCE(sat) v IC

VCE(sat) v IC



hFE v IC

VBE(sat) v IC



VBE(on) v IC

Safe Operating Area